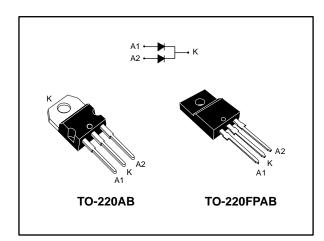


STPS20SM80C

Power Schottky rectifier

Datasheet - production data



Features

- High junction temperature capability
- Optimized trade-off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified
- Insulated package TO-220FPAB
 - Insulated voltage: 2000 V_{RMS} sine

Description

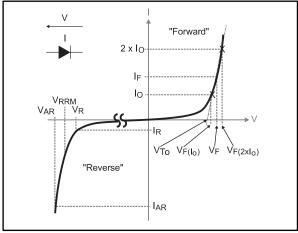
This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB and TO-220FPAB, this device is particularly suited for use in notebook, game station, LCD TV and desktop adapters, providing these applications with a good efficiency at both low and high load.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	2 x 10 A
V _{RRM}	80 V
T _i (max.)	175 °C
V _F (typ.)	515 mV

Figure 1: Electrical characteristics





 V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in Figure 10. V_{AR} and I_{AR} are pulse measurements ($t_p < 1 \ \mu s$). V_R , I_R , V_{RRM} and V_F , are static characteristics.

May 2017 DocID018720 Rev 2 1/10

Characteristics STPS20SM80C

1 Characteristics

Table 2: Absolute ratings (limiting values, per diode, at 25 °C, unless otherwise specified)

Symbol	Parameter				Value	Unit	
V _{RRM}	Repetitive peak reve	rse voltage			80	V	
I _{F(RMS)}	Forward rms current				30	Α	
		TO-220AB	T _C = 155 °C	Per diode	10		
	Average forward	10-220AB	T _C = 150 °C	Per device	20	Δ.	
I _{F(AV)}	current δ = 0.5, square wave	TO 000EDAD	T _C = 130 °C	Per diode	10	Α	
		TO-220FPAB	T _C = 100 °C	Per device	20		
IFSM	Surge non repetitive forward current		t _p = 10 ms sinusoidal		220	Α	
Parm ⁽¹⁾	Repetitive peak avalanche power		$t_p = 10 \ \mu s, \ T_j = 125 \ ^{\circ}C$		385	W	
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage		t_p < 1 μ s, T_j < 150 °C, I_{AR} < 16.2 A		100	>	
V _{ASM} ⁽²⁾	Maximum single pulse peak avalanche voltage		t_p < 1 μ s, T_j < 150 °C, I_{AR} < 16.2 A		100	V	
T _{stg}	Storage temperature range			-65 to +175	°C		
Tj	Maximum operating junction temperature (3)			175	°C		

Notes:

Table 3: Thermal parameters

Symbol	Parame	Max. value	Unit			
		TO-220AB	Per diode	2.30		
D	R _{th(j-c)} Junction to case	10-220AB	Total	1.55	°C/W	
Kth(j-c)		TO-220FPAB	Per diode	5.80		
		10-220FPAB	Total	4.65		
D	D Coupling			0.80	°C/W	
R _{th(c)}	Coupling	TO-220FPAB		3.50	C/VV	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_{j \; (diode1)} = P_{(diode1)} \; x \; R_{th(j-c)} \; (per \; diode) \; + \; P_{(diode2)} \; x \; R_{th(c)}$$

⁽¹⁾For pulse time duration deratings, please refer to figure 4. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

⁽²⁾See Figure 10

 $^{^{(3)}(}dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

STPS20SM80C Characteristics

Table 4: Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾ Reverse leakage curren	Devene leskens symmet	T _j = 25 °C	W W	-	5.8	25	μΑ
IR''	Reverse leakage current	T _j = 125 °C	$V_R = V_{RRM}$	-	5	15	mΑ
	$V_F^{(2)}$ Forward voltage drop $T_j = T_j = T$	T _j = 25 °C	I _F = 5 A	-	0.590	0.640	
		T _j = 125 °C		-	0.515	0.550	
V (2)		T _j = 25 °C	I _F = 10 A	-	0.710	0.780	\ /
VF ⁽²⁾		T _j = 125 °C		-	0.595	0.650	V
		T _j = 25 °C	1 20 A	-	0.850	0.945	
		T _j = 125 °C	I _F = 20 A	ı	0.690	0.780	

Notes:

 $^{(1)}$ Pulse test: t_p = 5 ms, δ < 2%

 $^{(2)} Pulse$ test: t_p = 380 $\mu s, \, \delta < 2\%$

To evaluate the conduction losses, use the following equation:

 $P = 0.52 \text{ x } I_{F(AV)} + 0.013 \text{ x } I_{F^2(RMS)}$

Characteristics STPS20SM80C

1.1 Characteristics (curves)

Figure 2: Average forward power dissipation

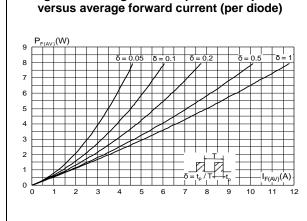


Figure 3: Average forward current versus ambient temperature (δ = 0.5, per diode)

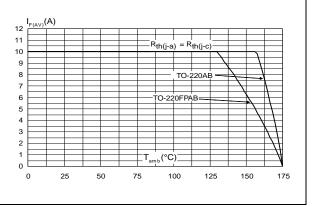


Figure 4: Normalized avalanche power derating versus pulse duration (T_j = 125 °C)

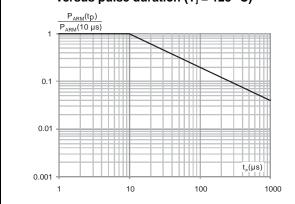


Figure 5: Relative thermal impedance junction to case versus pulse duration (TO-220AB)

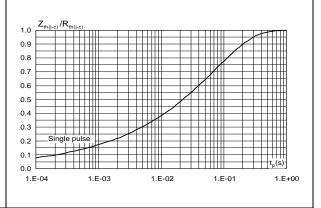


Figure 6: Relative thermal impedance junction to case versus pulse duration (TO-220FPAB)

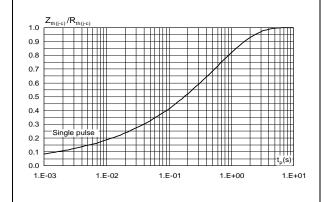
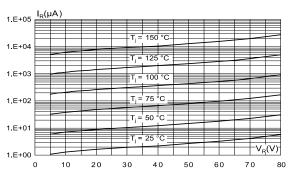
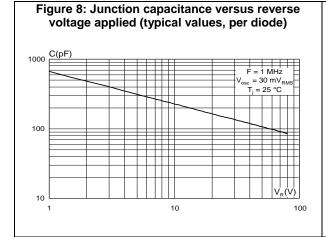


Figure 7: Reverse leakage current versus reverse voltage applied (typical values, per diode)



4/10 DocID018720 Rev 2

STPS20SM80C Characteristics



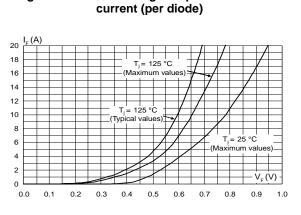
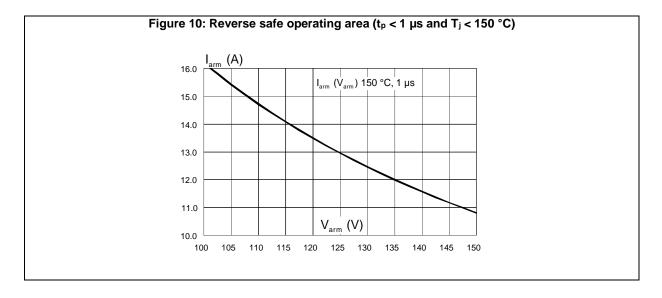


Figure 9: Forward voltage drop versus forward



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Cooling method: by conduction (C)
- Epoxy meets UL 94,V0
- Recommended torque value: 0.55 N⋅m (for TO-220AB and TO-220FPAB)
- Maximum torque value: 0.7 N·m (for TO-220AB and TO-220FPAB)

2.1 TO-220AB package information

b1(x3) — b (x3)

Figure 11: TO-220AB package outline

Table 5: TO-220AB package mechanical data

Dimensions				
Ref.	Millim	Millimeters		hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
b	0.61	0.88	0.240	0.035
b1	1.14	1.70	0.045	0.067
С	0.48	0.70	0.019	0.028
D	15.25	15.75	0.600	0.620
D1	1.27 typ.		0.050 typ.	
E	10.00	10.40	0.394	0.409
е	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
F	1.23	1.32	0.048	0.052
H1	6.20	6.60	0.244	0.260
J1	2.40	2.72	0.094	0.107
L	13.00	14.00	0.512	0.551
L1	3.50	3.93	0.138	0.155
L20	16.40 typ.		0.646 typ.	
L30	28.90 typ.		1.138 typ.	
θР	3.75	3.85	0.148	0.152
Q	2.65	2.95	0.104	0.116

Package information STPS20SM80C

2.2 TO-220FPAB package information

Figure 12: TO-220FPAB package outline

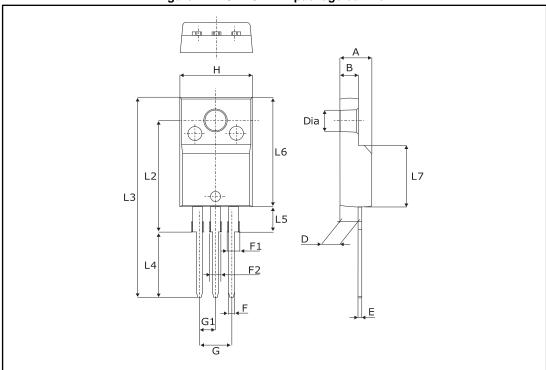


Table 6: TO-220FPAB package mechanical data

	Dimensions			
Ref.	Millim	Millimeters		hes
	Min. Max.		Min.	Max.
Α	4.40	4.60	0.173	0.181
В	2.5	2.7	0.098	0.106
D	2.50	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1.0	0.03	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.40	2.70	0.094	0.106
Н	10.00	10.40	0.393	0.409
L2	16.00	O typ.	0.63	typ.
L3	28.60	30.60	1.126	1.205
L4	9.80	10.6	0.386	0.417
L5	2.90	3.60	0.114	0.142
L6	15.90	16.40	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia	3.0	3.20	0.118	0.126

8/10 DocID018720 Rev 2

STPS20SM80C Ordering information

3 Ordering information

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS20SM80CT	PS20SM80CT	TO-220AB	1.9 g	50	Tube
STPS20SM80CFP	PS20SM80CFP	TO-220FPAB	1.9 g	50	Tube

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
11-Apr-2011	1	First issue.
12-May-2017	2	Removed D ² PAK and DPAK packages.

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